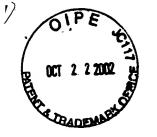
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In re Application of: Sh	nooshtarian, et a	I. OPE	()	Group Art Unit: _	2823	
Serial No.: 09/527,873				Examiner: H	sein-Ming Lee	
Filed: March 17, 2000		CI 1 TEE		Our Account No.	: 04-1403	i A
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Title: Localized Heatin	g and Cooling o	of Substrates	)			CX CEX
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hereby certify that this	correspondence	and any reference	ed anachmen	and fee are being der	osited with the	e United States Po
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Washington, DC 20231,	on October	<u>r 17, 2002</u>	·			•

Lyan Watkins

(Typed or printed name of person mailing paper or fee)

(Signature of person mailing paper or fee)





#22/AMOT D 10/29/07

**PATENT** 

ATTORNEY DOCKET NO.: AGX-37-RCE-CPA

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application ) Shooshtarian, et al. )	Examiner: Hsein-Ming Lee
Serial No.: 09/527,873 )	Art Unit: 2823
Filed: March 17, 2000 )	Dept. Acct. No.: 04-1403
Title: Localized Heating and ) Cooling of Substrates )	Dept. Acct. No.: 04-1403
Commissioner for Patents Washington, D.C. 20231	TER 280

## **AMENDMENT**

Dear Sir:

In response to the Office Action dated June 19, 2002, please amend the abovecaptioned applications as follows:

## **IN THE CLAIMS:**

Please add the following claims:

42. A method as defined in claim 1, wherein said gas used to selectively control the temperature of at least one of said localized regions is supplied by a device located below said semiconductor wafer.

43. A method as defined in claim 42, wherein said device is a reflective device through which a plurality of gas patiets extend.

44. A method as defined in claim 1, wherein said gas used to selectively control the temperature of at least one of said localized regions is supplied by a device located above said semiconductor wafer.

10/24/2002 HBERHE

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